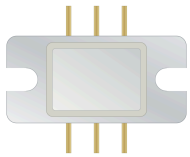
2000–8500 MHz GaN Packaged Power Amplifier — PSAT 41 dBm (typical)

LCI-PA-2000-8500-PS41T · 2000–8500 MHz · GaN Packaged Power Amplifier.



The RF table specifies: PSAT 41 dBm (typical); Power gain 15 dB (typical); PAE 35 % (typical). RF test conditions: TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 26 dBm; PW = 100 µs; D = 10%.

CMW010B

Apply gate bias before drain bias. Remove drain bias before gate bias.

Vg: C = 10 µF

Vg: 1, 3

RFin: 2

Vd: 4, 6

RFout: 5

Package outline dimensions: 18.03 × 8.7 mm.

RF characteristics

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 26 dBm; PW = 100 µs; D = 10%

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	2000	-	8500	MHz
Saturated output power	-	40.3	41	-	dBm
Power gain	-	14.3	15	-	dB
Power-added efficiency	-	25	35	-	%
Power-gain flatness	-	-	-	1.5	dB
Small-signal gain	-	20	22	24	dB

DC bias and current

Parameter	Symbol	Minimum	Typical	Maximum	Value	Unit
Drain voltage	-	-	-	-	28	V
Gate voltage	-	-	-	-	-2.6	V
Quiescent current	-	-	-	-	0.9 (Vd = 28 V)	A

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	-	-	-	32	V
Minimum gate bias	-	-5	-	-	V

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Storage temperature	-	-65	-	150	°C
Maximum input power	-	-	-	30	dBm
Maximum channel temperature	-	-	-	200	°C

Package outline dimensions

Parameter	Value	Unit
Package outline dimensions	18.03 × 8.7	mm
Terminal span	14.7	mm

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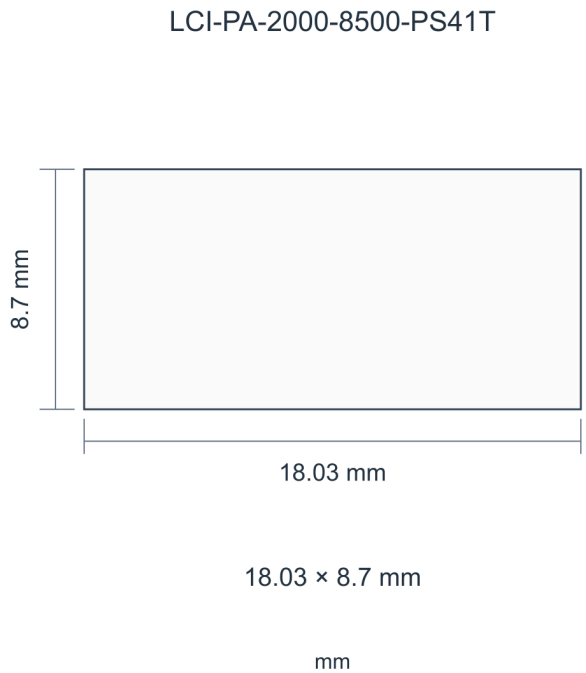
Integration notes

CMW010B Apply gate bias before drain bias. Remove drain bias before gate bias. Vg: C = 10 µF Vg: 1, 3 RFin: 2 Vd: 4, 6 RFout: 5

Mechanical Outline

Partial drawing showing confirmed dimensions in mm. Use the complete installation drawing for installation.

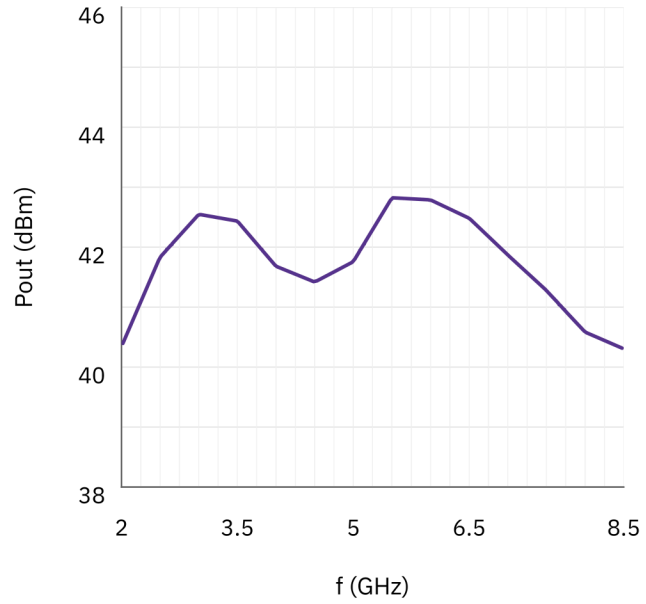


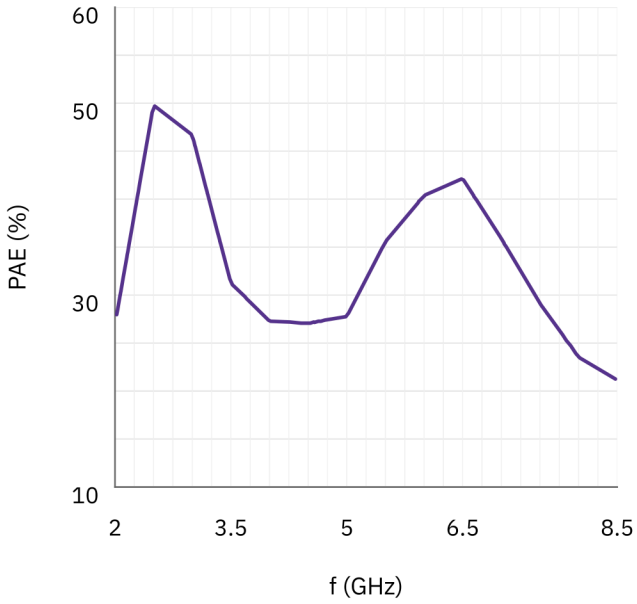
Performance curves

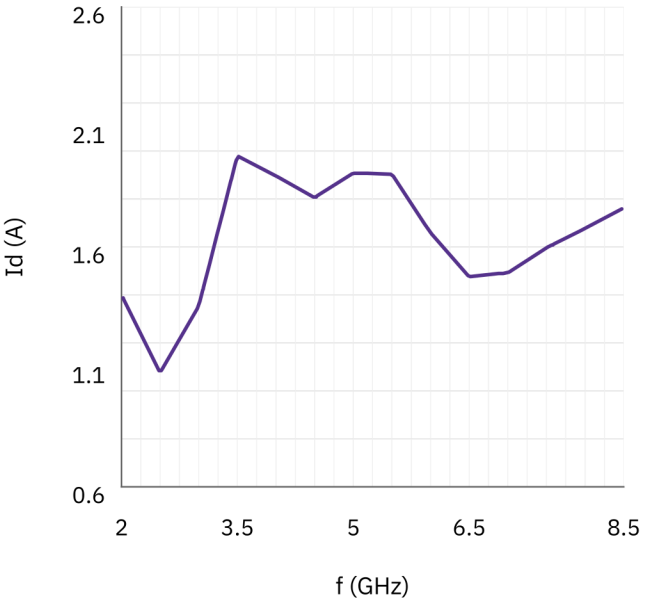
Each performance plot applies to its stated operating conditions.

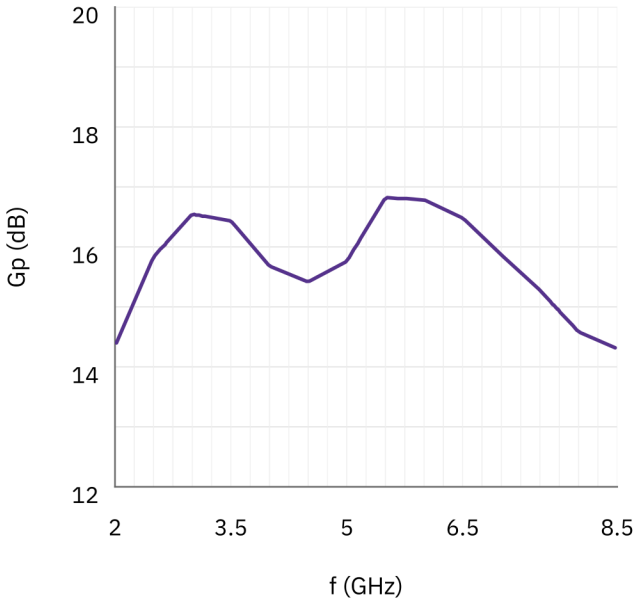
Pulsed — Output power; Power-added efficiency; Dynamic drain current; Power gain.

Figure notes: TA=+25°C; Vd=+28V; Vg=-2.6V; Pin=26dBm. Readings are approximate. τ = 100 µs; D = 10%.



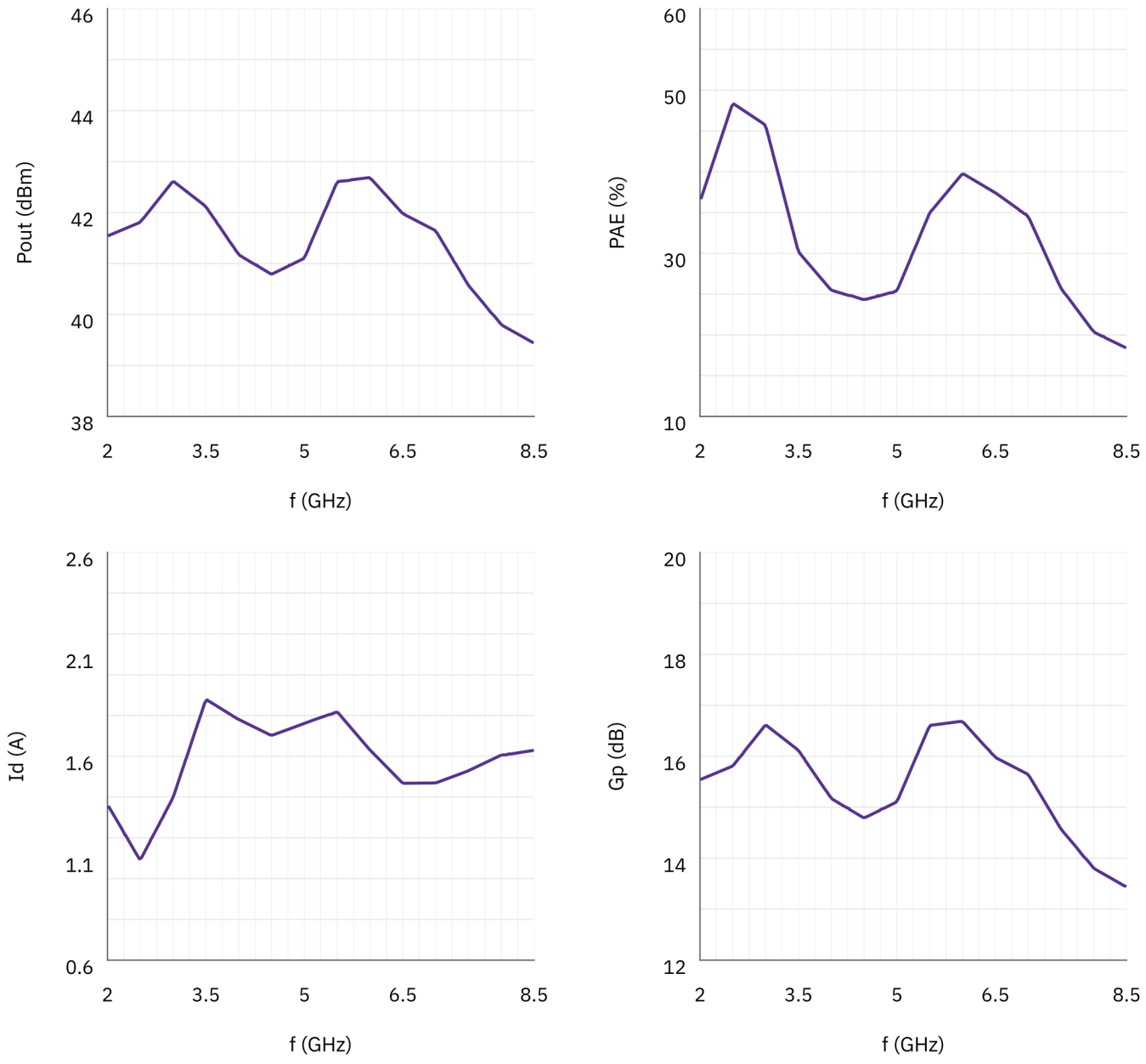






Continuous wave (CW) — Pout; PAE; Id; Gp.

Figure notes: TA=+25°C; Vd=+28V; Vg=-2.6V; Pin=26dBm. Readings are approximate. The upper-left plot shows Pout in dBm. The lower-right plot shows Gp in dB.



Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.